

34. (Twice Amended) A semiconductor device comprising:

- a semiconductor substrate;
- a first insulating film formed on said semiconductor substrate;
- a first conductor formed on said semiconductor substrate through said first insulating film;
- a first upper wire formed on said first insulating film and said first conductor; and
- a second insulating film formed on said first upper wire and over said first insulating film, said second insulating film including a thin area over said first conductor for guiding a laser beam;
- a second conductor formed on said semiconductor substrate through said first insulating film below the thin area; and
- a second upper wire formed on an extension line of said first upper wire on said first insulating film and said second conductor beneath said second insulating film.

35. (Amended) A semiconductor device comprising:

- a semiconductor substrate;
- a first insulating film formed on said semiconductor substrate;
- a first conductor formed on said semiconductor substrate through said first insulating film, including a first portion formed on said semiconductor substrate and a second portion formed on the first portion made of a different material from that of the first portion;
- a first upper wire formed on said first insulating film and said first conductor; and

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com